(19) World Intellectual Property Organization

International Bureau



(43) International Publication Date 31 March 2005 (31.03.2005)

(10) International Publication Number WO 2005/028697 A1

(51) International Patent Classification?: 16/00, 8/00, H01L 21/306, C23F 1/00

C23C 14/34,

(21) International Application Number:

PCT/US2004/029744

(22) International Filing Date:

13 September 2004 (13.09.2004)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

60/502,782

12 September 2003 (12.09.2003)

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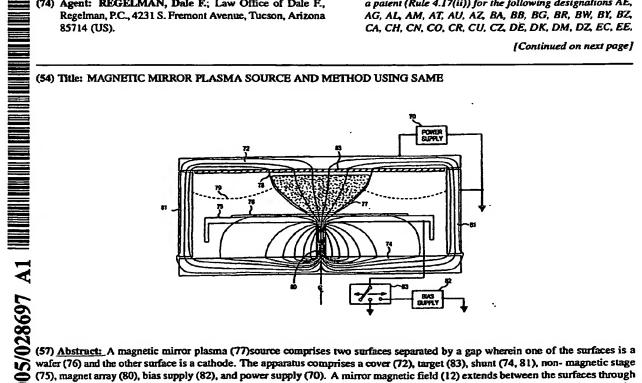
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- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declarations under Rule 4.17:

as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii)) for the following designations AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ,



wafer (76) and the other surface is a cathode. The apparatus comprises a cover (72), target (83), shunt (74, 81), non-magnetic stage (75), magnet array (80), bias supply (82), and power supply (70). A mirror magnetic field (12) extends between the surfaces through the gap, wherein the magnetic field (78) lines at the substrate surface are at least two times as strong as those field lines entering the cathode. An anode is disposed such that a closed loop electron Hall current containment region is formed within the magnetic field, where with sufficient gas pressure and voltage between the cathode and anode, plasma is formed in the containment region. The result is a novel plasma source that has unique and important advantages enabling advancements in PECVD, etching, sputtering and plasma treatment processes.